# 2SA1550

# Silicon PNP triple diffusion planar type

### For power switching

### Features

- High foward current transfer ratio h<sub>FE</sub>
- High-speed switching
- ullet High collector to base voltage  $V_{CBO}$
- I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings (T<sub>C</sub>=25°C)

| Parameter                            | Symbol           | Ratings     | Unit |  |
|--------------------------------------|------------------|-------------|------|--|
| Collector to base voltage            | V <sub>CBO</sub> | -400        | V    |  |
| Collector to emitter voltage         | V <sub>CEO</sub> | -400        | V    |  |
| Emitter to base voltage              | V <sub>EBO</sub> | -7          | V    |  |
| Peak collector current               | $I_{CP}$         | -1.0        | A    |  |
| Collector current                    | $I_{C}$          | - 0.5       | A    |  |
| Collector power T <sub>C</sub> =25°C | D                | 15          | W    |  |
| dissipation Ta=25°C                  | $P_{C}$          | 1.3         | W    |  |
| Junction temperature                 | T <sub>j</sub>   | 150         | °C   |  |
| Storage temperature                  | T <sub>stg</sub> | -55 to +150 | C C  |  |

# 7.0±0.3 3.5±0.2 1.1±0.1 0.85±0.1 0.4±0.1 1.2 3 1:Base 2:Collector 3:Emitter 1 Type Package Unit: mm 3.5±0.2 Unit: mm 3.5±0.2 Unit: mm 3.5±0.2 1:Base 2:Collector 3:Emitter 1 Type Package (Y)

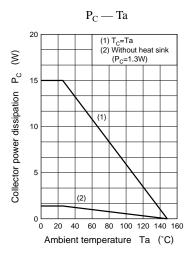
# Electrical Characteristics (T<sub>C</sub>=25°C)

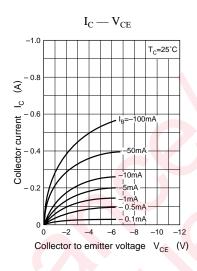
| Parameter                               | Symbol               | Conditions                                       | min              | typ  | max  | Unit |
|---|----------------------|--|------------------|------|------|------|
| Collector cutoff current                | $I_{CBO}$            | $V_{CB} = -400V, I_E = 0$                        | \<br>\<br>\<br>\ |      | -100 | μA   |
| Emitter cutoff current                  | $I_{EBO}$            | $V_{EB} = -7V, I_C = 0$                          | 7.90             |      | -100 | μΑ   |
| Collector to emitter voltage            | $V_{CEO}$            | $I_{C} = -10 \text{mA}, I_{B} = 0$               | -400             |      |      | V    |
| Forward current transfer ratio          | h <sub>FE1</sub> *   | $V_{CE} = -5V, I_{C} = -50mA$                    | 80               |      | 280  |      |
|   | h <sub>FE2</sub>     | $V_{CE} = -5V, I_{C} = -300mA$                   | 10               |      |      |      |
| Collector to emitter saturation voltage | V <sub>CE(sat)</sub> | $I_C = -200 \text{mA}, I_B = -40 \text{mA}$      |                  |      | -1.5 | V    |
| Base to emitter saturation voltage      | V <sub>BE(sat)</sub> | $I_C = -200 \text{mA}, I_B = -40 \text{mA}$      |                  |      | -1.5 | V    |
| Transition frequency                    | $f_T$                | $V_{CE} = -10V, I_C = -100mA, f = 1MHz$          |                  | 20   |      | MHz  |
| Turn-on time                            | t <sub>on</sub>      | $I_{C} = -300 \text{mA},$                        |                  | 0.25 |      | μs   |
| Storage time                            | t <sub>stg</sub>     | $I_{B1} = -60 \text{mA}, I_{B2} = 60 \text{mA},$ |                  | 2.0  |      | μs   |
| Fall time                               | $t_{\rm f}$          | $V_{CC} = -200V$                                 |                  | 0.5  |      | μs   |

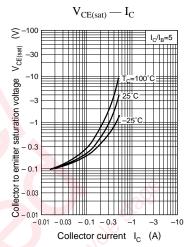
### \*h<sub>FE1</sub> Rank classification

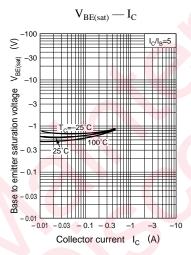
| Rank      | Q         | P          |
|-----------|-----------|------------|
| $h_{FE1}$ | 80 to 160 | 130 to 280 |

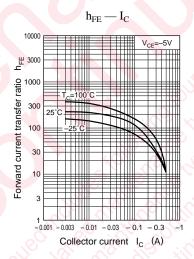
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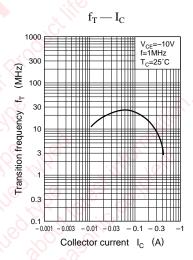


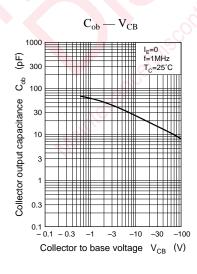


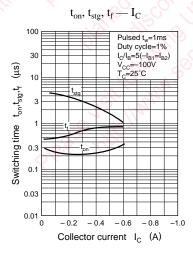


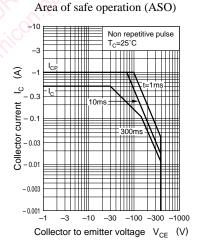






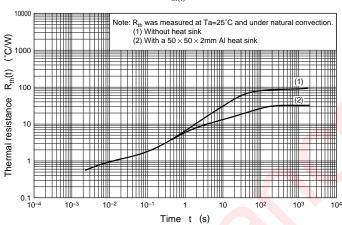






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